

LRS1306 Stacked Chip

APPLICATIONS:

Pager
PDA
Set Top Box
Cellular Phone

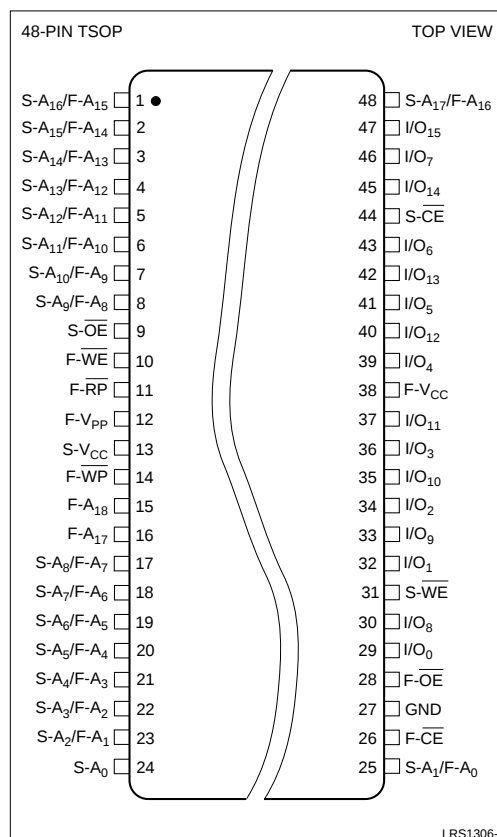
FEATURES

- 8M Flash and 2 M SRAM
- Flash memory access time 120 ns MAX.
- SRAM access time 85 ns MAX.
- Operating current
 - Flash memory read 25 mA MAX. ($t_{\text{CYCLE}} = 200 \text{ ns}$)
 - Flash word write 57 mA MAX. ($F\text{-}V_{\text{CC}} \geq 3.0 \text{ V}$)
 - Flash block erase 42 mA MAX. ($F\text{-}V_{\text{CC}} \geq 3.0 \text{ V}$)
 - SRAM operating 25 mA MAX. ($t_{\text{CYCLE}} = 200 \text{ ns}$)
- Standby current
 - Flash memory 25 μA MAX.
($F\text{-}\overline{\text{CE}} \geq F\text{-}V_{\text{CC}} - 0.2 \text{ V}$, $F\text{-}\overline{\text{RP}} \leq 0.2 \text{ V}$, $F\text{-}V_{\text{PP}} \leq 0.2 \text{ V}$)
 - SRAM 120 μA MAX. ($S\text{-}\overline{\text{CE}} \geq S\text{-}V_{\text{CC}} - 0.2 \text{ V}$)
1.0 μA TYP. ($T_A = 25^\circ\text{C}$, $S\text{-}V_{\text{CC}} = 3 \text{ V}$, $S\text{-}\overline{\text{CE}} \geq S\text{-}V_{\text{CC}} - 0.2 \text{ V}$)
 - Total standby current is the summation of flash memory's standby current and SRAM's standby current
- Power supply 2.7 V to 3.6 V.
- Operating temperature -40°C to $+85^\circ\text{C}$
 - Block erase and word write operations of flash memory with $T_A < -30^\circ\text{C}$ are Not Supported
- Fully static operation
- Three-state output
- Not designed or rated as radiation hardened
- 48-pin TSOP (TSOP48-P-1014) plastic package
- Flash Memory has P-type bulk silicon, and SRAM has N-type bulk silicon

DESCRIPTION

The LRS1306 is a combination memory organized as $524,288 \times 8$ bit flash memory and $262,144 \times 8$ bit static RAM in one package. It is fabricated using silicon-gate CMOS process technology.

48-PIN TSOP PINOUT



PIN DESCRIPTION

PIN	DESCRIPTION
S-A ₁ /F-A ₀ to S-A ₁₇ /F-A ₁₆	Common Address Input Pins
S-A ₀	Address Input Pin for SRAM
F-A ₁₇ to F-A ₁₈	Address Input Pin for Flash Memory
F- $\overline{\text{CE}}$	Chip Enable Input Pin for Flash Memory
S- $\overline{\text{CE}}$	Chip Enable Input Pin for SRAM
F- $\overline{\text{WE}}$	Write Enable Input Pin for Flash Memory
S- $\overline{\text{WE}}$	Write Enable Input Pin for SRAM
F- $\overline{\text{OE}}$	Output Enable Input Pin for Flash Memory
S- $\overline{\text{OE}}$	Output Enable Input Pin for SRAM
I/O ₀ to I/O ₇	Common Data Input/Output Pins
I/O ₈ to I/O ₁₅	Data Input/Output Pins for Flash Memory
F- $\overline{\text{RP}}$	Reset/Deep Power Down Input Pin for Flash Memory
F- $\overline{\text{WP}}$	Write Protect Pin for Flash Memory's Boot Block
F-V _{CC}	Power Supply Pin for Flash Memory
F-V _{PP}	Power Supply for Flash Memory Write/Erase
S-V _{CC}	Power Supply Pin for SRAM
GND	Common GND